

Ingo Tischer

List of Publications by Year in descending order

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docs citations

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citing authors

#	ARTICLE	IF	CITATIONS
1	Three-dimensional cathodoluminescence characterization of a semipolar GaInN based LED sample. Journal of Applied Physics, 2017, 121, .	2.5	5
2	Evidence of terbium and oxygen co-segregation in annealed AlN:Tb. Applied Physics Letters, 2017, 110, .	3.3	5
3	Composition analysis of coaxially grown InGaN multi quantum wells using scanning transmission electron microscopy. Journal of Applied Physics, 2016, 119, 175701.	2.5	0
4	Stacking fault emission in GaN: Influence of n-type doping. Journal of Applied Physics, 2016, 119, .	2.5	5
5	EBIC investigations on polar and semipolar InGaN LED structures. Physica Status Solidi (B): Basic Research, 2016, 253, 126-132.	1.5	7
6	Determination of axial and lateral exciton diffusion length in GaN by electron energy dependent cathodoluminescence. Journal of Applied Physics, 2016, 120, .	2.5	14
7	Optical properties of defects in nitride semiconductors. Journal of Materials Research, 2015, 30, 2977-2990.	2.6	5
8	Optical gas sensing by micro-photoluminescence on multiple and single ZnO nanowires. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1810-1816.	1.8	11
9	Measurement of the diffusion length and the lifetime of free excitons in gallium nitride using cathodoluminescence under different conditions of luminescence excitation. Journal of Surface Investigation, 2015, 9, 839-843.	0.5	1
10	Crystal quality improvement of semipolar (20-21) GaN on patterned sapphire substrates by in-situ deposited SiN mask. , 2014, , .		0
11	Nanoscale characterisation of semiconductors by cathodoluminescence. IOP Conference Series: Materials Science and Engineering, 2014, 55, 012018.	0.6	8
12	Basal plane stacking faults in semipolar AlGaIn: Hints to Al redistribution. Physica Status Solidi (B): Basic Research, 2014, 251, 2321-2325.	1.5	5
13	GaN tubes with coaxial non- and semipolar GaInN quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 648-651.	0.8	6
14	(Invited) Large Area Semipolar GaN Grown on Foreign Substrates. ECS Transactions, 2014, 61, 101-107.	0.5	0
15	INGAN/GAN based semipolar green converters. Journal of Crystal Growth, 2013, 370, 120-123.	1.5	3
16	Coaxial InGaN epitaxy around GaN micro-tubes: Tracing the signs. Journal of Crystal Growth, 2013, 370, 319-322.	1.5	3
17	Optical Properties of ZnO/GaN/InGaN Core-Shell Nanorods. Japanese Journal of Applied Physics, 2013, 52, 075201.	1.5	1
18	Three-dimensional reciprocal space mapping of diffuse scattering for the study of stacking faults in semipolar (11 $\bar{2}$) GaN layers grown from the sidewall of an <i>x</i>-patterned sapphire substrate. Journal of Applied Crystallography, 2013, 46, 1425-1433.	4.5	11

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19	Studies on Defect Reduction in AlGaIn Heterostructures by Integrating an In-situ SiN Interlayer. Japanese Journal of Applied Physics, 2013, 52, 08JJ07.	1.5	6
20	Semipolar GaInN quantum well structures on large area substrates. Physica Status Solidi (B): Basic Research, 2012, 249, 464-467.	1.5	7
21	Suppression of gallium inhomogeneity in ZnO nanostructures on GaN using seed layers. Materials Letters, 2012, 83, 31-34.	2.6	1
22	Luminescence properties of epitaxially grown GaN and InGaIn layers around ZnO nanopillars. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1582-1585.	1.8	5
23	Stacking fault-related luminescence features in semi-polar GaN. Physica Status Solidi (B): Basic Research, 2011, 248, 611-615.	1.5	12
24	Catalytic growth of hexagonally aligned ZnO nanorods. Physica Status Solidi (B): Basic Research, 2011, 248, 1915-1918.	1.5	5
25	Light-emitting diode based on mask- and catalyst-free grown N-polar GaN nanorods. Nanotechnology, 2011, 22, 265202.	2.6	9
26	$I \propto \frac{1}{L^2}$ plane stacking fault in GaN: Origin of the 3.32 eV luminescence band. Physical Review B, 2011, 83, .	3.2	16
27	Cathodoluminescence of GaInN quantum wells grown on nonpolar a plane GaN: Intense emission from pit facets. Applied Physics Letters, 2010, 97, 101904.	3.3	14
28	Cathodoluminescence and photoluminescence study on AlGaIn layers grown with SiNx interlayers. Applied Physics Letters, 2010, 97, .	3.3	12
29	Structural and cathodoluminescence properties of ZnO nanorods after Ga-implantation and annealing. Journal of Applied Physics, 2009, 105, .	2.5	8